



SOT-23 Plastic-Encapsulate MOSFETS

CJ2333 P-Channel MOSFET

DESCRIPTION

The CJ2333 uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

FEATURE

- TrenchFET Power MOSFET

APPLICATION

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

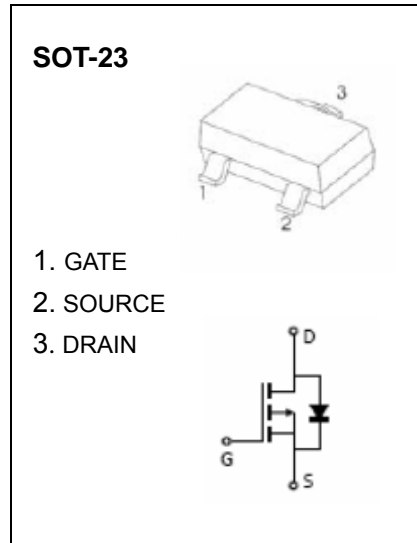
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MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	I_D	-6 ^a	A
Pulsed Drain Current ($t=300\mu\text{s}$)	I_{DM}	-20	A
Power Dissipation	P_D	0.35 ^b	W
		1.1 ^a	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357 ^b	$^{\circ}\text{C}/\text{W}$
		113 ^a	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}\text{C}$

a. Device mounted on FR-4 substrate board, with minimum recommended pad layout, single side.

b. Device mounted on no heat sink.



ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-12			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -12V, V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±8V, V _{DS} = 0V			±0.1	μA
Gate threshold voltage (note 1)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.4		-1	V
Drain-source on-resistance (note 1)	R _{DS(on)}	V _{GS} = -4.5V, I _D = -5A			28	mΩ
		V _{GS} = -3.7V, I _D = -4.6A			32	
		V _{GS} = -2.5V, I _D = -4.3A			40	
		V _{GS} = -1.8V, I _D = -1A			63	
		V _{GS} = -1.5V, I _D = -0.5A			150	
Forward tranconductance (note 1)	g _{FS}	V _{DS} = -5V, I _D = -5A		18		S
Dynamic characteristics (note 2)						
Input Capacitance	C _{iss}	V _{DS} = -6V, V _{GS} = 0V, f = 1MHz		1275		pF
Output Capacitance	C _{oss}			255		pF
Reverse Transfer Capacitance	C _{rss}			236		pF
Gate resistance	R _g	f = 1MHz	1.9		19	Ω
Total Gate Charge	Q _g	V _{DS} = -6V, V _{GS} = -4.5V, I _D = -5A		14	21	nC
Gate-Source Charge	Q _{gs}			2.3		nC
Gate-Drain Charge	Q _{gd}			3.6		nC
Turn-on delay time	t _{d(on)}	V _{DD} = -6V, V _{GEN} = -4.5V, I _D = -4A R _L = 6Ω, R _{GEN} = 1Ω		26	40	ns
Turn-on rise time	t _r			24	40	ns
Turn-off delay time	t _{d(off)}			45	70	ns
Turn-off fall time	t _f			20	35	ns
Source-Drain Diode characteristics						
Diode forward current	I _S	T _C = 25°C			-1.4	A
Diode pulsed forward current	I _{SM}				-20	A
Diode Forward voltage (note 1)	V _{DS}	V _{GS} = 0V, I _S = -4A			-1.2	V
Diode reverse recovery time (note 2)	t _{rr}	I _F = -4A, dI/dt = 100A/μs		24	48	ns
Diode reverse recovery charge (note 2)	Q _{rr}				8	16

- Notes :**
1. Pulse test; pulse width ≤ 300μs, duty cycle ≤ 2%.
 2. Guaranteed by design, not subject to production testing.

Typical Characteristics

CJ2333

